优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

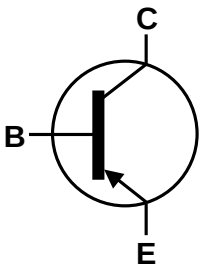
- BV_{CEO} > -30V
- I_C = -1A High Continuous Current
- Excellent h_{FE} Characteristics up to -2A
- Low Saturation Voltage $V_{CE(sat)}$ < -0.5V @ -1A

Mechanical Data

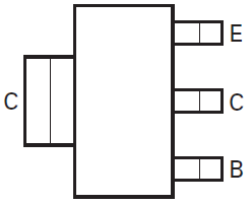
- Case: SOT223
- Case Material: Molded Plastic. “Green” Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208e3
- Weight: 0.112 grams (Approximate)

SOT223

Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-1	A
Peak Pulse Current	I_{CM}	-2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

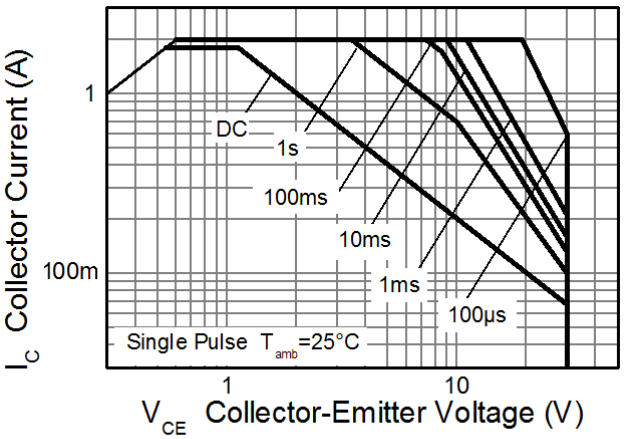
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	2	W
	(Note 6)		3	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	62.5	°C/W
	(Note 6)		41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)		$R_{\theta JL}$	19.4	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

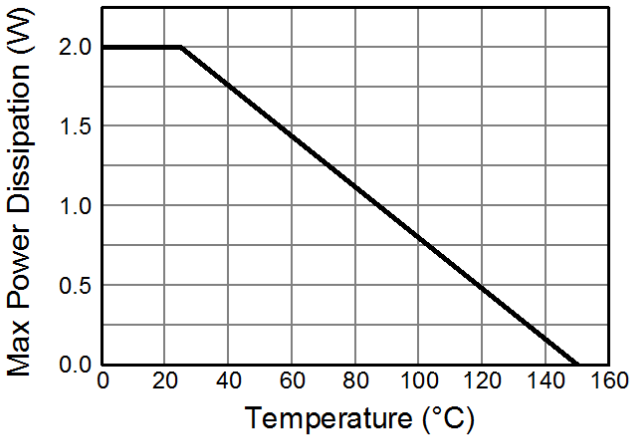
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device is mounted on 50mm x 50mm single sided 2oz weight copper.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

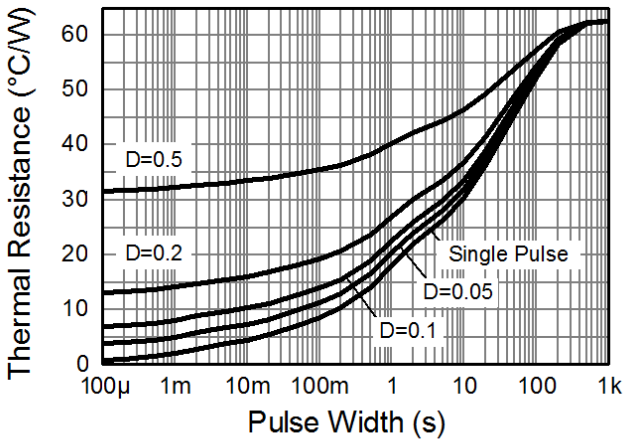
Thermal Characteristics and Derating Information



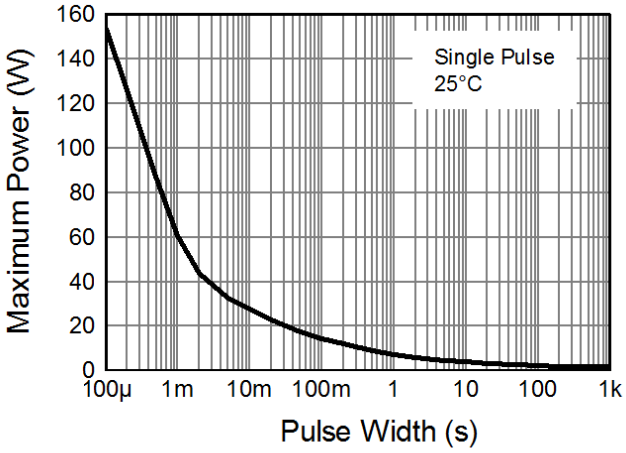
Safe Operating Area



Derating Curve



Transient Thermal Impedance



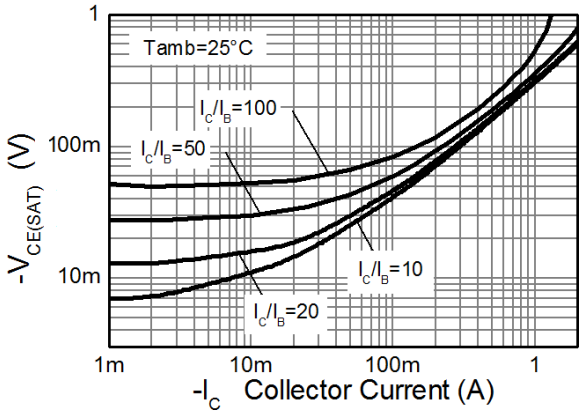
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

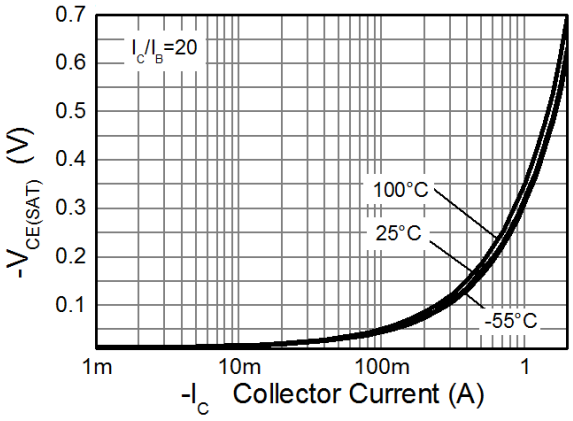
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-35	–	–	V	I_C = -100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	-30	–	–	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	–	–	V	I_E = -100μA
Collector Cut-Off Current	I_{CBO}	–	–	-100 -10	nA uA	V_{CB} = -30V V_{CB} = -30V, T_{amb} = +100°C
Collector Cut-Off Current	I_{CES}	–	–	-100	nA	V_{CES} = -30V
Emitter Cut-Off Current	I_{EBO}	–	–	-100	nA	V_{EB} = -4V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	– –	– –	-0.50 -0.75	V	I_C = -1A, I_B = -100mA I_C = -2A, I_B = -200mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	–	–	-1.25	V	I_C = -1A, I_B = -100mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	–	–	-1.0	V	I_C = -1A, V_{CE} = -2V
DC Current Transfer Static Ratio (Note 9)	h_{FE}	70 100 80 30	– – – –	– 300 – –	-	I_C = -50mA, V_{CE} = -2V I_C = -500mA, V_{CE} = -2V I_C = -1A, V_{CE} = -2V I_C = -2A, V_{CE} = -2V
Transitional Frequency (Note 9)	f_T	100	–	–	MHz	V_{CE} = -5V, I_C = -100mA f = 100MHz
Output Capacitance (Note 9)	C_{obo}	–	–	10	pF	V_{CB} = -10V. f = 1MHz
Switching Times	t_{on}	–	50	-	ns	I_C = -500mA, V_{CC} = -10V I_{B1} = I_{B2} = -50mA
	t_{off}		300			

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

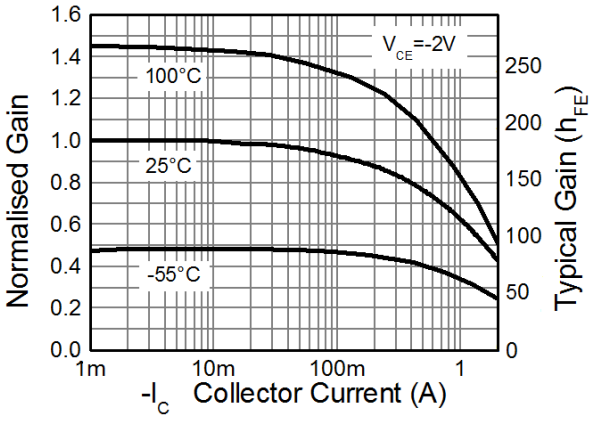
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



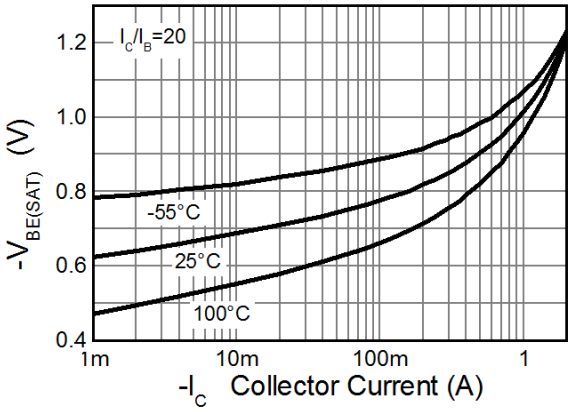
$V_{CE(SAT)}$ v I_C



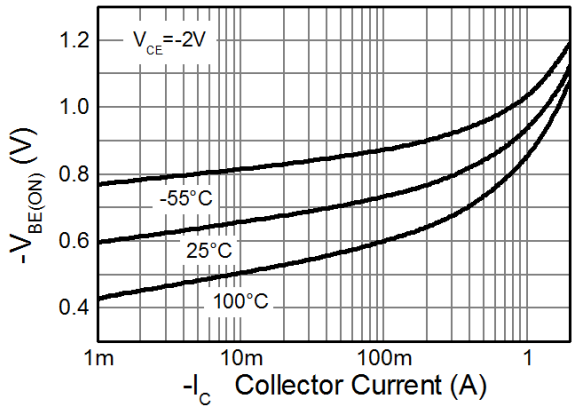
$V_{CE(SAT)}$ v I_C



h_{FE} v I_C

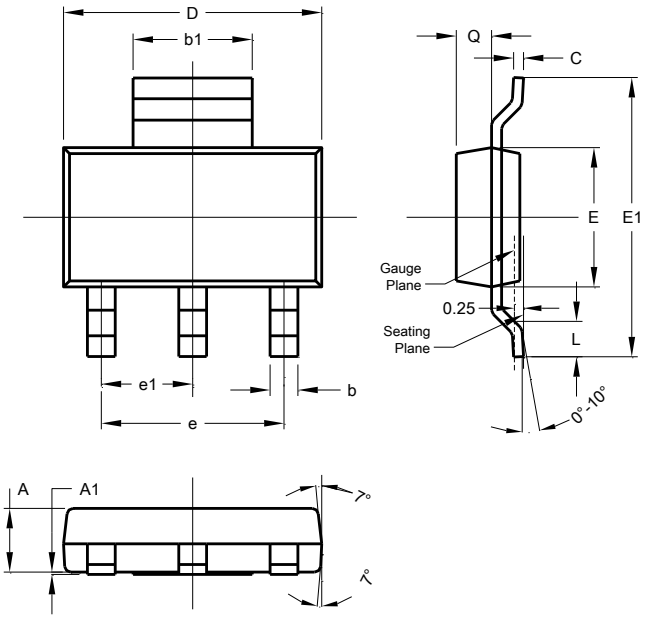


$V_{BE(SAT)}$ v I_C



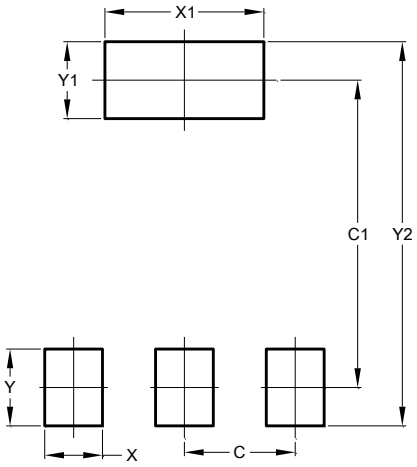
$V_{BE(ON)}$ v I_C

Package Outline Dimensions



SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00